



**GaN on SiC HEMT Pulsed Power Transistor**  
**250W Peak, 960-1215 MHz, 128µs Pulse, 10% Duty**

**Production V1**  
**18 Aug 11**

## Features

- GaN depletion mode HEMT microwave transistor
- Internally matched
- Common source configuration
- Broadband Class AB operation
- RoHS Compliant
- +50V Typical Operation
- MTTF of 114 years (Channel Temperature < 200°C)

## Applications

- Avionics: Mode-S, TCAS, JTIDS, DME and TACAN.

## Product Description

The MAGX-000912-250L00 is a gold metalized matched Gallium Nitride (GaN) on Silicon Carbide RF power transistor optimized for civilian and military pulsed avionics amplifier applications the 960 MHz to 1215 MHz range such as Mode-S, TCAS, JTIDS, DME and TACAN . Using state of the art wafer fabrication processes, these high performance transistors provide high gain, efficiency, bandwidth, ruggedness over a wide bandwidth for today's demanding application needs. High breakdown voltages allow for reliable and stable operation in extreme mismatched load conditions unparalleled with older semiconductor technologies.



## Typical RF Performance at Pout = 250W Peak

Freq (MHz)	Pin (W)	Gain (dB)	Slope (dB)	Id (A)	Eff (%)	Avg-Eff (%)	RL (dB)	Droop (dB)
960	3.4	18.7	-	8.5	58.8	-	-8.8	0.4
1030	4.2	17.8	-	8.3	60.1	-	-12.7	0.4
1090	3.4	18.7	-	8.2	61.1	-	-9.3	0.4
1150	3.4	18.7	-	8.2	60.7	-	-8.6	0.3
1215	3.5	18.6	1.0	8.6	58.0	59.7	-11.5	0.4

## Ordering Information

MAGX-000912-250L00 250W GaN Power Transistor  
 MAGX-000912-SB1PPR Evaluation Fixture

1

**ADVANCED:** Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

**PRELIMINARY:** Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

• **North America** Tel: 800.366.2266 / Fax: 978.366.2266  
 • **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300  
 • **Asia/Pacific** Tel: 81.44.844.8296 / Fax: 81.44.844.8298  
 Visit [www.macomtech.com](http://www.macomtech.com) for additional data sheets and product information.

*M/A-COM Technology Solutions and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.*

**GaN on SiC HEMT Pulsed Power Transistor**  
**250W Peak, 960-1215 MHz, 128 $\mu$ s Pulse, 10% Duty**

**Production V1**  
**18 Aug 11**

**Absolute Maximum Ratings Table (1, 2, 3)**

Supply Voltage ( $V_{DD}$ )	+65V
Supply Voltage ( $V_{GS}$ )	-8 to -2V
Supply Current ( $I_{D_{MAX}}$ )	14.2 Apk
Input Power ( $P_{IN}$ )	+40 dBm
Absolute Max. Junction/Channel Temp	200 °C
MTTF ( $T_J < 200^\circ\text{C}$ )	114 years
Pulsed Power Dissipation at 85°C	460 Wpk
Thermal Resistance, ( $T_J = 70^\circ\text{C}$ ) $V_{DD} = 50\text{V}$ , $I_{DQ} = 250\text{mA}$ , $P_{out} = 250\text{W}$ 128 $\mu$ s Pulse / 10% Duty	0.25°C/W
Operating Temp	-40 to +95°C
Storage Temp	-65 to +150°C
Mounting Temperature	See solder reflow profile
ESD Min. - Machine Model (MM)	50V
ESD Min. - Human Body Model (HBM)	>250V
MSL Level	MSL1

(1) Operation of this device above any one of these parameters may cause permanent damage.

(2) Channel temperature directly affects a device's MTTF. Channel temperature should be kept as low as possible to maximize lifetime.

(3) For saturated performance it recommended that the sum of ( $3 \cdot V_{DD} + \text{abs}(V_{GG})$ ) < 175

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
<b>DC CHARACTERISTICS</b>						
Drain-Source Leakage Current	$V_{GS} = -8\text{V}$ , $V_{DS} = 175\text{V}$	$I_{DS}$	-	0.4	12	mA
Gate Threshold Voltage	$V_{DS} = 5\text{V}$ , $I_D = 30\text{mA}$	$V_{GS(th)}$	-5	-3.1	-2	V
Forward Transconductance	$V_{DS} = 5\text{V}$ , $I_D = 7.0\text{mA}$	$G_M$	5.0	7.7	-	S
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	Not applicable—Input internally matched	$C_{ISS}$	N/A	N/A	N/A	pF
Output Capacitance	$V_{DS} = 50\text{V}$ , $V_{GS} = -8\text{V}$ , $F = 1\text{MHz}$	$C_{OSS}$	-	22	-	pF
Feedback Capacitance	$V_{DS} = 50\text{V}$ , $V_{GS} = -8\text{V}$ , $F = 1\text{MHz}$	$C_{RSS}$	-	2.2	-	pF

**GaN on SiC HEMT Pulsed Power Transistor**  
**250W Peak, 960-1215 MHz, 128µs Pulse, 10% Duty**

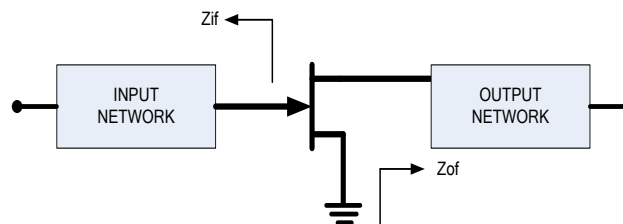
**Production V1**  
**18 Aug 11**

**Electrical Specifications:  $T_C = 25 \pm 5^\circ\text{C}$  (Room Ambient )**

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
<b>RF FUNCTIONAL TESTS (<math>V_{DD} = 50\text{V}</math>, <math>I_{DQ} = 250\text{mA}</math>, 128us / 10% duty, 960-1215MHz)</b>						
Input Power	$P_{out} = 250\text{W Peak (25W avg)}$	$P_{IN}$	-	3.5	5.3	Wpk
Power Gain	$P_{out} = 250\text{W Peak (25W avg)}$	$G_P$	16.7	18.5	-	dB
Drain Efficiency	$P_{out} = 250\text{W Peak (25W avg)}$	$\eta_D$	52	59.7	-	%
Load Mismatch Stability	$P_{out} = 250\text{W Peak (25W avg)}$	VSWR-S	5:1	-	-	-
Load Mismatch Tolerance	$P_{out} = 250\text{W Peak (25W avg)}$	VSWR-T	10:1	-	-	-

## Test Fixture Impedance

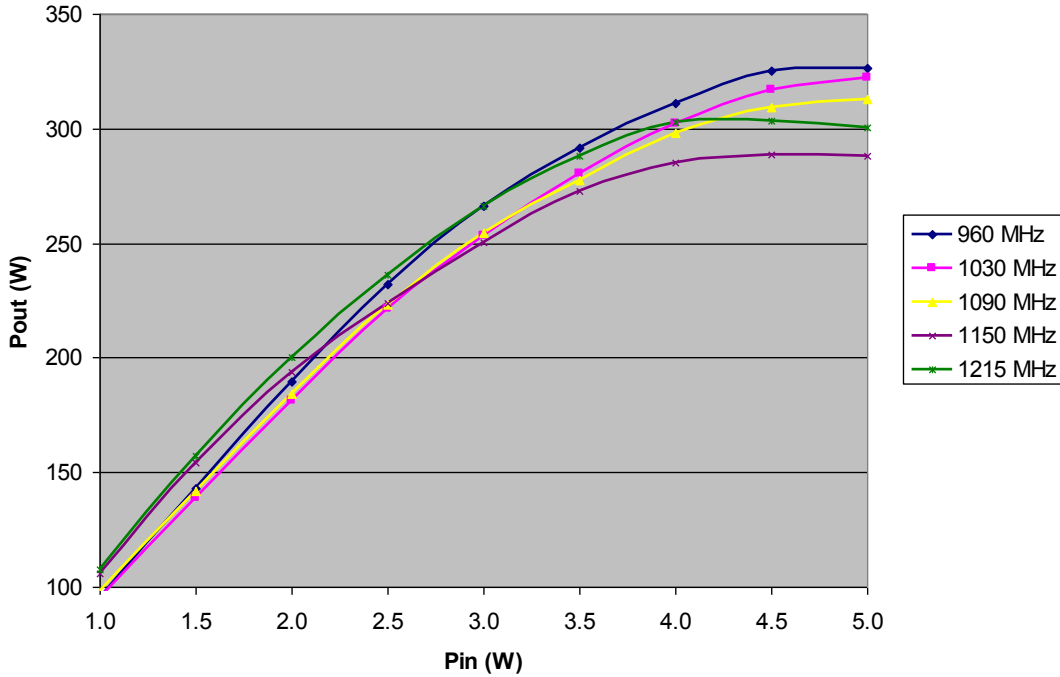
F (MHz)	$Z_{IF} (\Omega)$	$Z_{OF} (\Omega)$
960	2.6 - j4.6	4.0 + j0.0
1030	2.8 - j3.6	3.7 - j0.4
1090	2.8 - j3.9	3.6 - j0.4
1150	2.7 - j3.5	3.5 - j0.4
1215	2.8 - j3.1	3.6 - j0.5



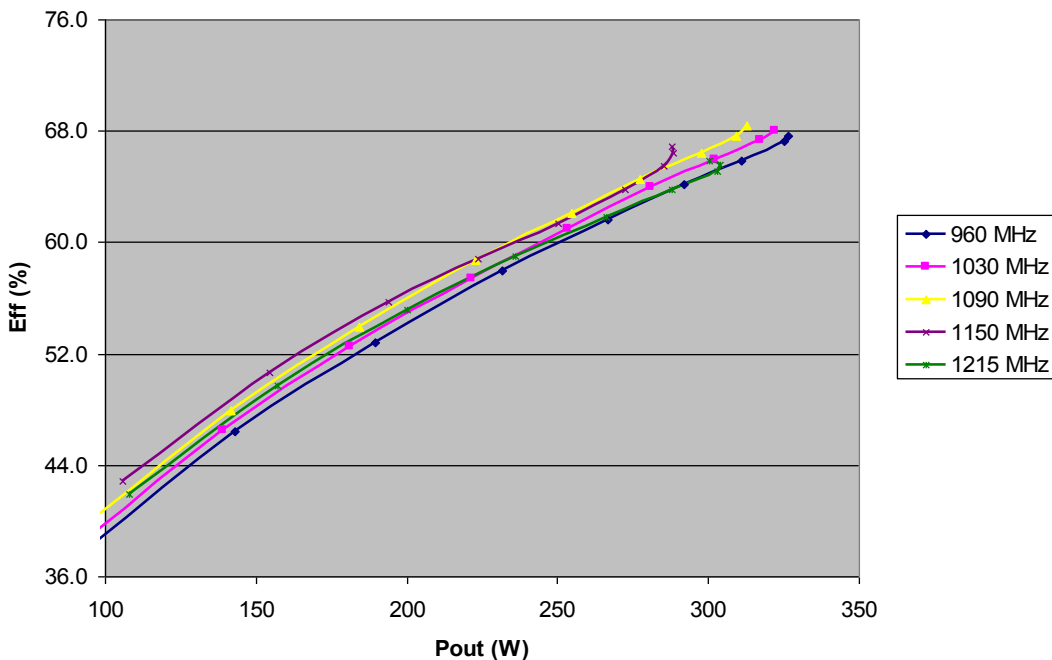
GaN on SiC HEMT Pulsed Power Transistor  
 250W Peak, 960-1215 MHz, 128µs Pulse, 10% Duty

Production V1  
 18 Aug 11

RF Power Transfer Curve (Output Power Vs. Input Power)



RF Power Transfer Curve (Drain Efficiency Vs. Output Power)



**ADVANCED:** Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

**PRELIMINARY:** Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

- **North America** Tel: 800.366.2266 / Fax: 978.366.2266
- **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- **Asia/Pacific** Tel: 81.44.844.8296 / Fax: 81.44.844.8298

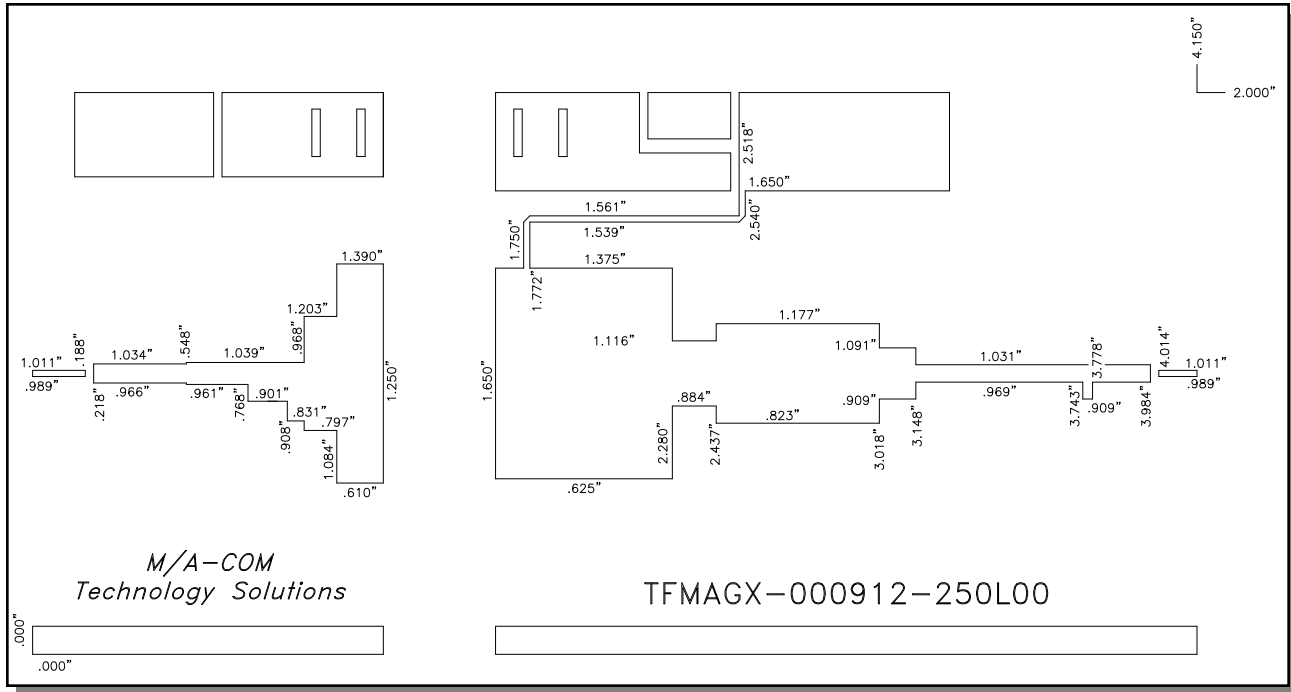
Visit [www.macomtech.com](http://www.macomtech.com) for additional data sheets and product information.

M/A-COM Technology Solutions and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

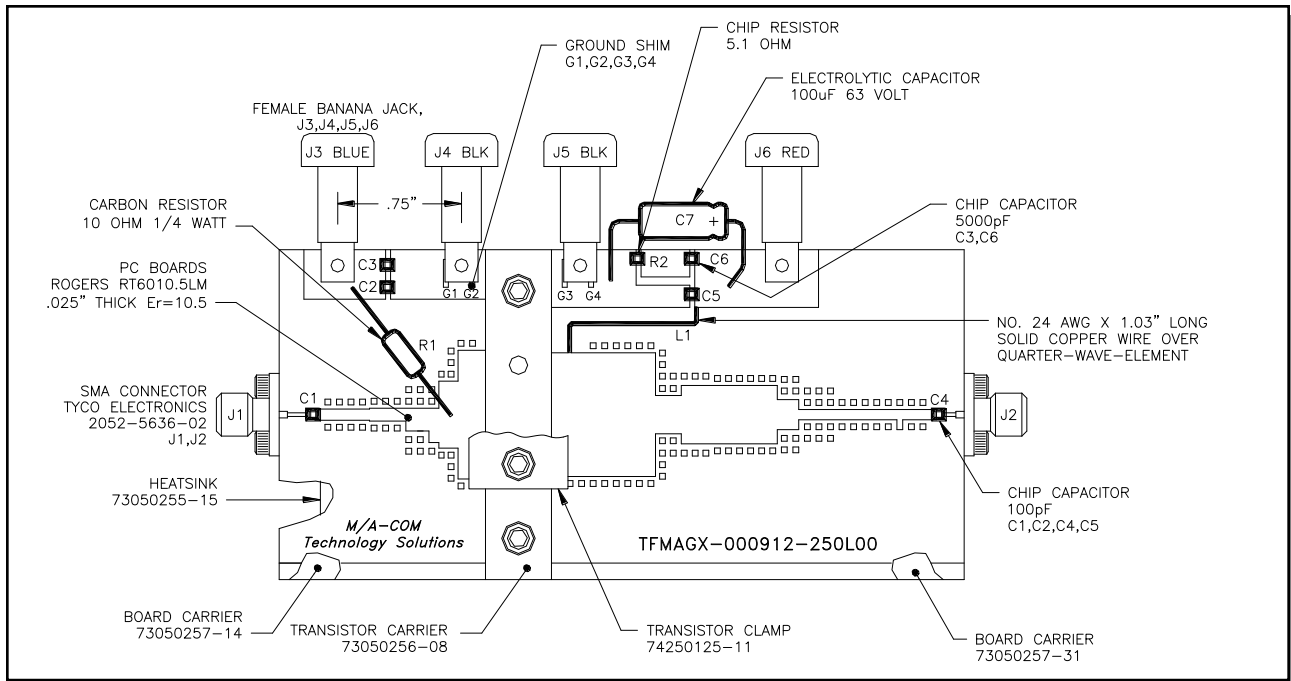
**GaN on SiC HEMT Pulsed Power Transistor**  
**250W Peak, 960-1215 MHz, 128µs Pulse, 10% Duty**

**Production V1**  
**18 Aug 11**

## Test Fixture Circuit Dimensions



## Test Fixture Assembly



**ADVANCED:** Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

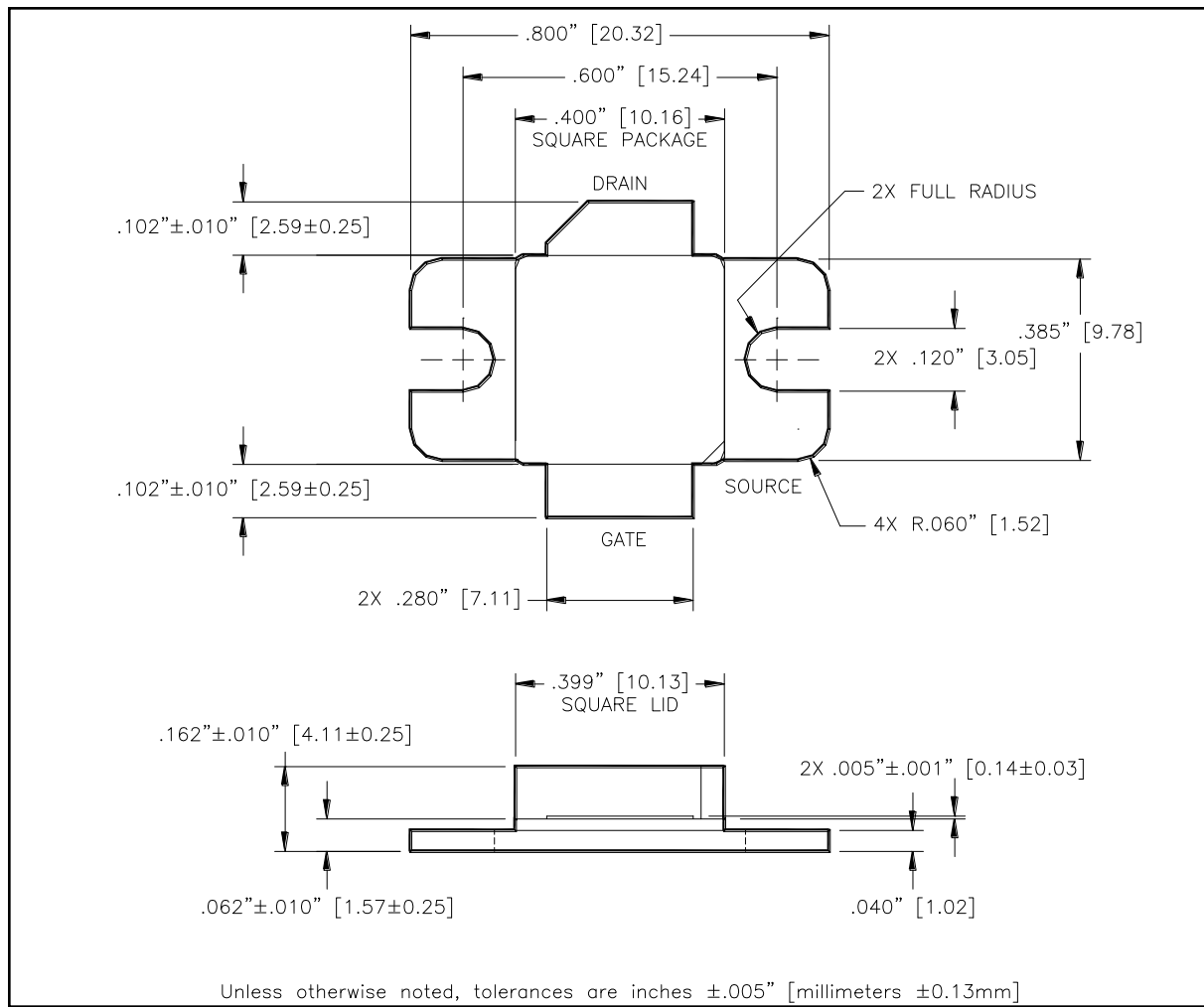
**PRELIMINARY:** Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

- **North America** Tel: 800.366.2266 / Fax: 978.366.2266
- **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- **Asia/Pacific** Tel: 81.44.844.8296 / Fax: 81.44.844.8298

Visit [www.macomtech.com](http://www.macomtech.com) for additional data sheets and product information.

M/A-COM Technology Solutions and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

Outline Drawing



CORRECT DEVICE SEQUENCING

TURNING THE DEVICE ON

1. Set  $V_{GS}$  to the pinch-off ( $V_P$ ), typically -5V
2. Turn on  $V_{DS}$  to nominal voltage (50V)
3. Increase  $V_{GS}$  until the  $I_{DS}$  current is reached
4. Apply RF power to desired level

TURNING THE DEVICE OFF

1. Turn the RF power off
2. Decrease  $V_{GS}$  down to  $V_P$
3. Decrease  $V_{DS}$  down to 0V
4. Turn off  $V_{GS}$